

Supplementary Information for

Centrosymmetric TiS as a novel topological electronic material
with coexisting type-I, type-II and hybrid nodal line states

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I. Band Structures of TiS under Different U Values

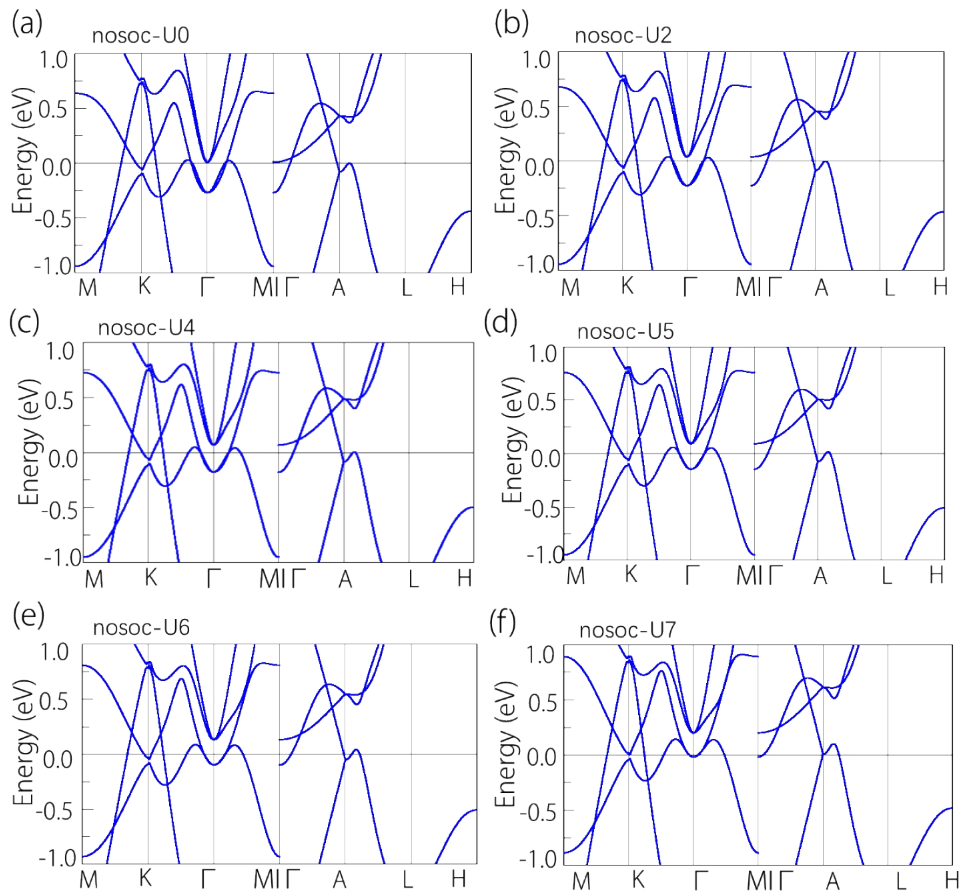


Figure S1. The band structures of TiS when the U values are chosen as (a) 0, (b) 2, (c) 4, (d) 5, (e) 6 and (f) 7 eV.